

# Technologies for the CLIC tracker

Andreas Nürnberg (CERN)  
on behalf of the CLICdp collaboration

12th Trento Workshop on Advanced Silicon Radiation Detectors  
Trento, Italy  
20. – 22. February 2017

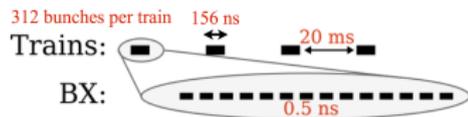
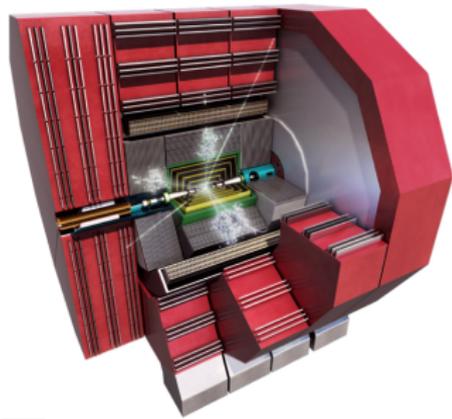


# Outline

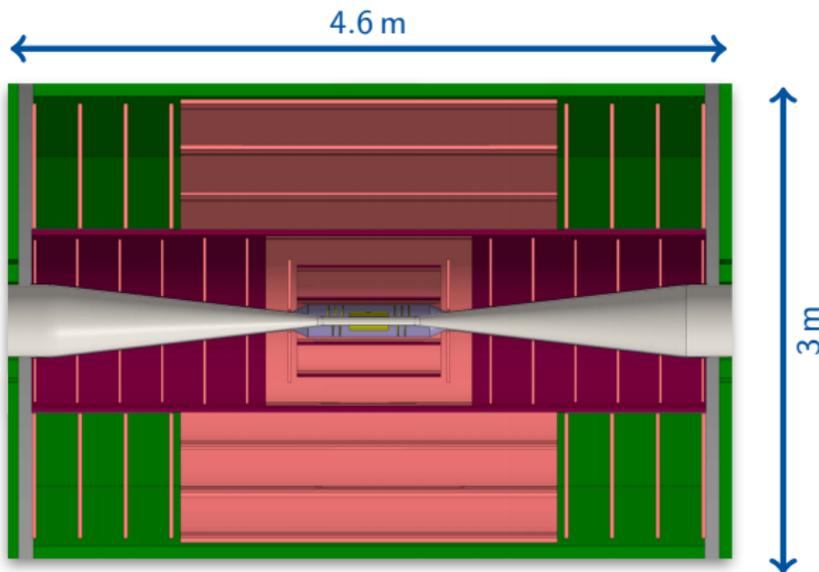
- ▶ CLIC tracker requirements, detector layout
- ▶ Investigated monolithic technologies
- ▶ Examples of ongoing analyses
  - ▶ ALICE investigator HR CMOS test chip
  - ▶ Cracow SOI chip

# Detector requirements - experimental conditions

- ▶ All-silicon tracker,  $1\%X_0 - 1.5\%X_0$  per detection layer
- ▶ Good momentum resolution,  
 $\sigma_{p_T}/p_T^2 = 2 \times 10^{-5} \text{ GeV}^{-1}$ 
  - ▶ 4 T field, 1.5 m tracker radius
  - ▶  $7 \mu\text{m}$  single point resolution
- ▶ No trigger, full readout of 156 ns bunch train
- ▶ Beam induced background:
  - ▶ High rate -  $3 \gamma\gamma \rightarrow$  hadron events per bunch crossing at 3 TeV
  - ▶ Requires high readout granularity
  - ▶ Requires precise timing  $\leq 10 \text{ ns}$
- ▶ Relaxed radiation environment:
  - ▶  $10^{-4}$  LHC levels



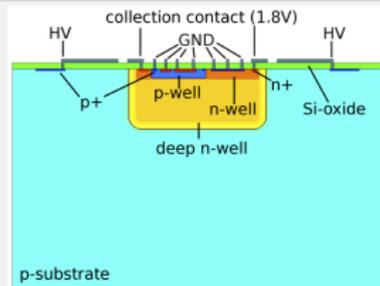
# Tracking detector layout



- ▶ Barrel: 3 inner, 3 outer layers
- ▶ Endcaps: 7 inner (6 short strips, 1 pixel), 4 outer discs per side
- ▶  $\sim 100 \text{ m}^2$  active area  $\rightarrow$  monolithic detector advantageous

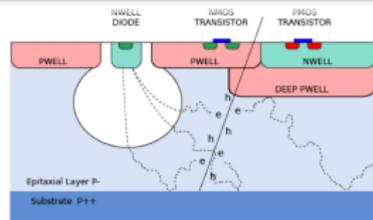
# Technology options under study

## HV-CMOS



- ▶ Large deep n-well for signal collection
- ▶ PMOS transistors embedded in n-well
- ▶ Drift and diffusion
- ▶ → Covered in previous talk by D. Hynds

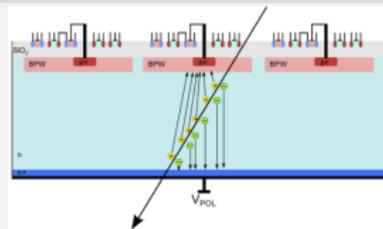
## HR-CMOS



W. Snoeys et al.

- ▶ Small n-well for signal collection
- ▶ PMOS/NMOS transistors embedded in n/p-wells
- ▶ Recent process modification → full-depletion possible

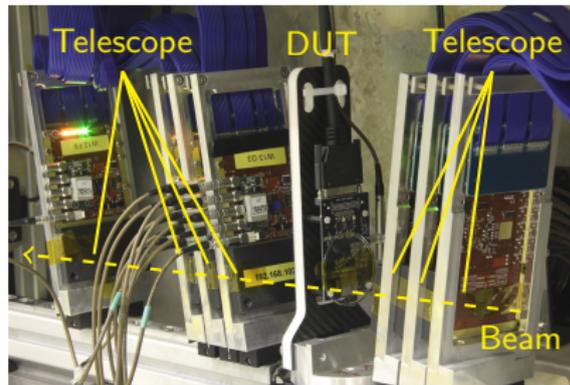
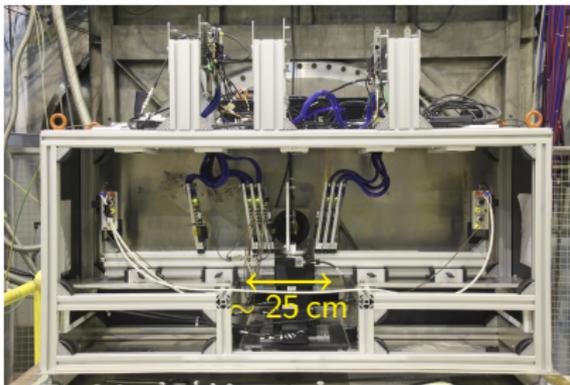
## SOI



- ▶ High-resistivity sensor wafer, CMOS electronics separated by oxide layer
- ▶ Full depletion

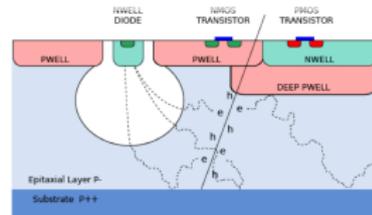
# Timepix3 Telescope

- ▶ Operated in H6 beamline at CERN SPS, 120 GeV pions
- ▶ 7 planes of Timepix3 assemblies (300  $\mu\text{m}$  thick, 55  $\mu\text{m}$  pitch, p-in-n sensors) for reference tracking
- ▶ Spatial resolution:  $\sim 2 \mu\text{m}$  on DUT
- ▶ Timing resolution:  $\lesssim 1 \text{ ns}$  on DUT, each pixel hit is time tagged with 1.56 ns clock
- ▶ Rate:  $\sim 1 \times 10^6$  Tracks/s



# ALICE Investigator

- ▶ TowerJazz 180 nm High-Resistivity CMOS
  - ▶ 15  $\mu\text{m}$  to 40  $\mu\text{m}$  thick / 1  $\text{k}\Omega\text{cm}$  to 8  $\text{k}\Omega\text{cm}$  epitaxial layer
  - ▶ Full CMOS: n-wells shielded by deep p-wells
- ▶ ALICE Investigator analog test chip
  - ▶ 134 pixel matrices, each  $8 \times 8$  pixels
  - ▶ Pixel sizes:  $20 \times 20 \mu\text{m}^2$  to  $50 \times 50 \mu\text{m}^2$
  - ▶ Access to time resolved waveform directly after the first amplifier
  - ▶ Select one matrix, readout of each pixel with external sampling ADCs



W. Snoeys et al.

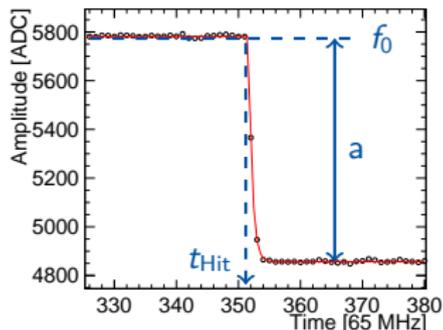
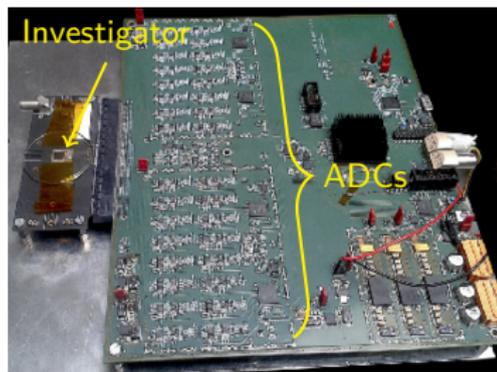


*NIM A 765 (2014) 177*

# Event reconstruction

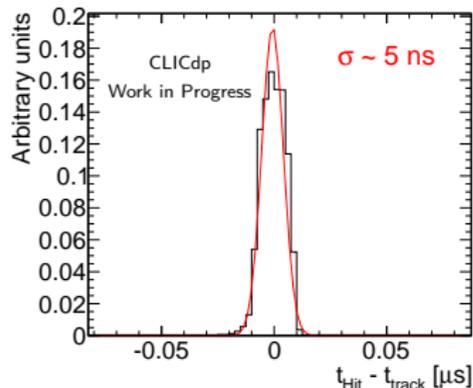
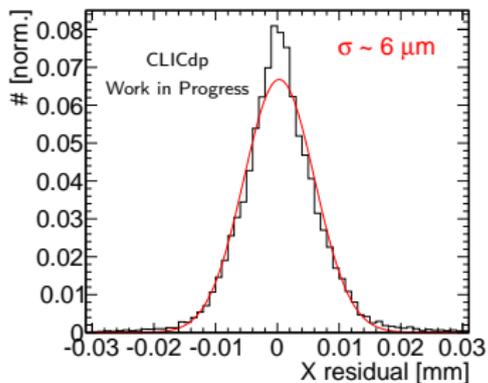
- ▶ Readout designed by ALICE
- ▶ 64 external sampling ADCs, one per pixel
- ▶ 1024 samples/frame/pixel, 65 MHz sampling
- ▶ Readout is triggered, if at least one pixel passes a predefined threshold
- ▶ Synchronized to telescope data stream
- ▶ Fit waveform to extract signal, absolute time and rise time

$$f(t) = \begin{cases} f_0 & t < t_0 \\ f_0 + a \left( \exp\left(-\frac{t-t_{\text{Hit}}}{\tau}\right) - 1 \right) & t \geq t_0 \end{cases}$$



# Resolution in space and time

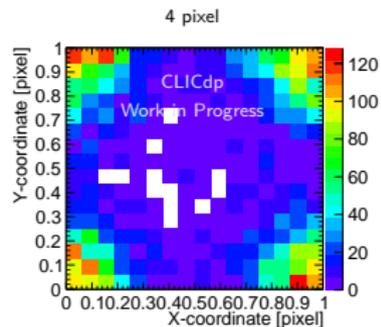
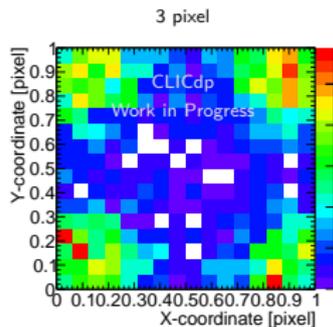
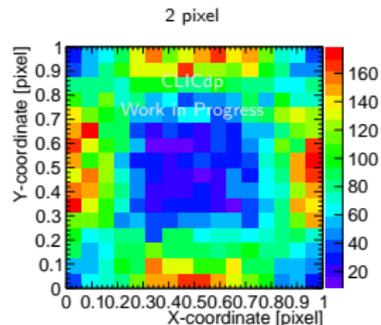
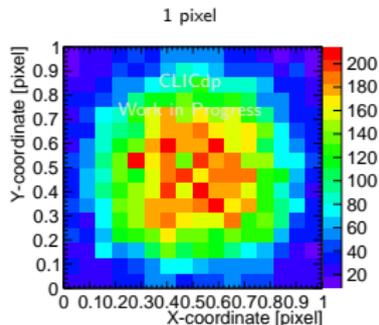
- ▶ 28  $\mu\text{m}$  pixel size, 6 V bias, modified process



- ▶ Compare extrapolated track impact position to reconstructed position
- ▶ Spatial resolution  $\sim 6 \mu\text{m}$ , telescope resolution not unfolded
- ▶ Compare extrapolated track time to reconstructed time
- ▶ Timing resolution  $\sim 5 \text{ ns}$ , dominated by the 65 MHz sampling of the readout

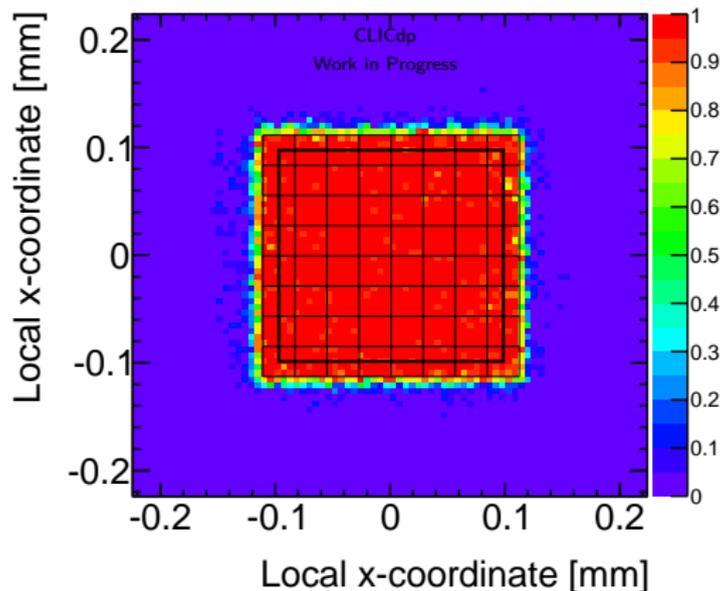
# Cluster size

- ▶ 28  $\mu\text{m}$  pixel size, 6 V bias, modified process
- ▶ Good pointing resolution of the telescope allows for sub-pixel resolved studies
- ▶ Track intercept in pixel cell for different cluster sizes
- ▶ Charge sharing to neighboring pixels at the edges and corners of the pixel cell



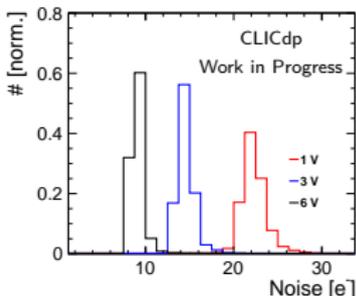
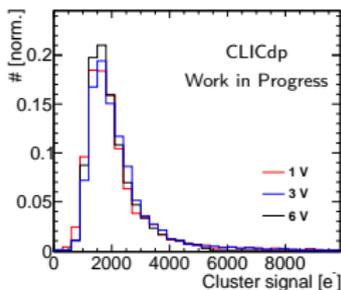
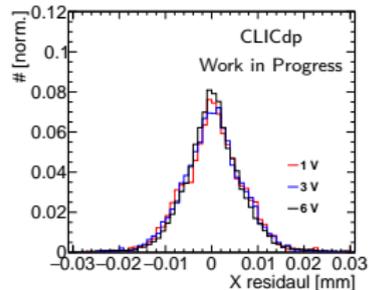
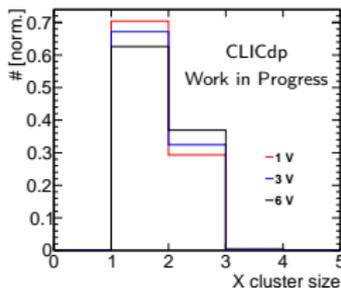
# Efficiency

- ▶ 28  $\mu\text{m}$  pixel size, 6 V bias, modified process
- ▶ Detection efficiency within the active time-period of the pixel matrix: 99.3 %
- ▶ Safety margin to the edges of 0.5 pixels to avoid edge effects
- ▶ Threshold:  $S/N > 8$



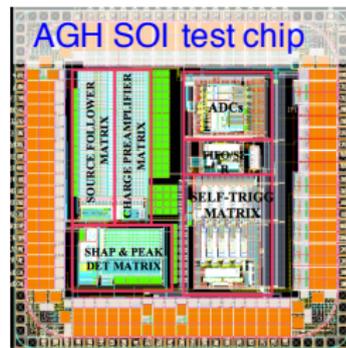
# Bias dependence

- ▶ 28  $\mu\text{m}$  pixel size, modified process
- ▶ Cluster size only slightly affected by bias voltage
- ▶ Calibrated cluster signal unchanged
- ▶ Spatial resolution unchanged
- ▶ Noise is decreasing with bias voltage, S/N is increasing



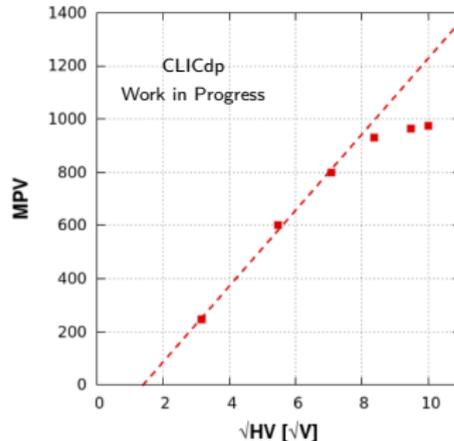
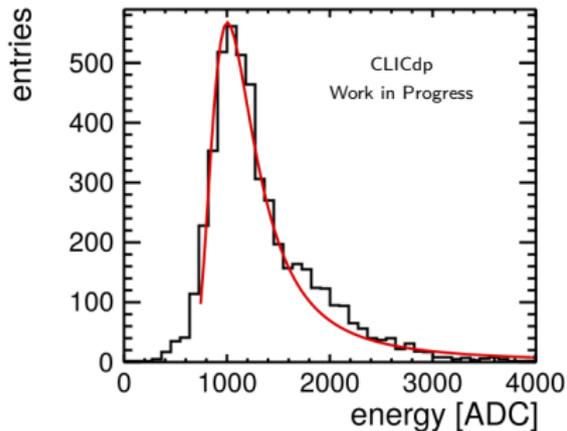
# Cracow SOI chip in Lapis 200 nm SOI

- ▶ CMOS sensor on Silicon On Insulator (SOI) wafers
- ▶ Electronics on low resistivity wafer, separated by buried oxide from fully depleted high-resistivity sensing layer
- ▶ Technology allows to fabricate thin sensors - down to  $50\ \mu\text{m}$
- ▶ Test-chip from AGH Cracow
  - ▶ Different pixel sizes ( $\geq 30 \times 30\ \mu\text{m}^2$ ) and readout techniques (source follower, charge preamp., self-triggering, ...)
- ▶ In this study focus on source follower matrix on FZ-n wafer
- ▶ Rolling shutter readout (integration time for one frame:  $150\ \mu\text{s}$ )



# SOI results

- ▶ FZ-n, 500  $\mu\text{m}$  thick, source follower matrix, 30  $\mu\text{m}$  pixel size

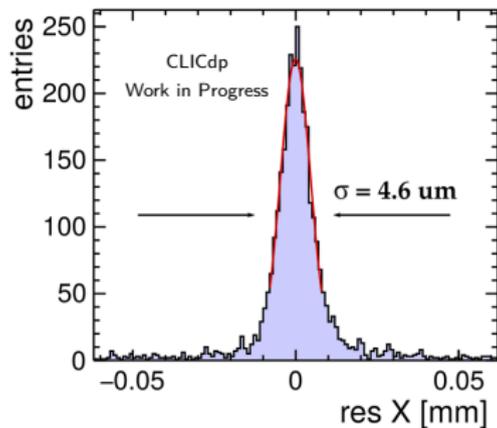


- ▶ Energy spectrum after clusterization
- ▶ All hits, no track matching

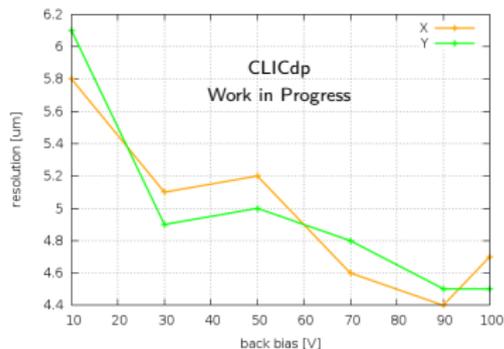
- ▶ Full depletion around 80 V

# SOI results

- ▶ FZ-n, 500  $\mu\text{m}$  thick, source follower matrix, 30  $\mu\text{m}$  pixel size



- ▶ Spatial resolution  $\sim 4.6 \mu\text{m}$  at 90 V, telescope resolution not unfolded
- ▶ Benefit from charge sharing in thick sensor



- ▶ Resolution is improving, as sensor volume gets depleted

# Summary & outlook

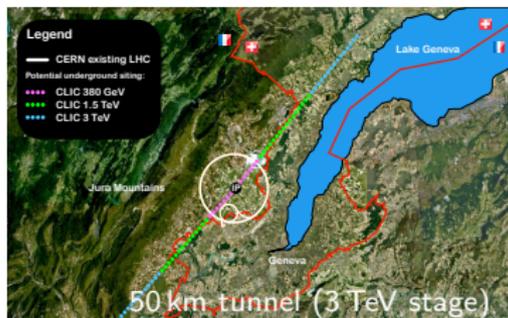
- ▶ Investigating various fully integrated CMOS technologies for the CLIC tracker
  - ▶ HV-CMOS studied in capacitively coupled devices (→ talk by D. Hynds)
  - ▶ ALICE Investigator HR-CMOS test chip
  - ▶ SOI pixel prototype chip
- ▶ Ongoing: comparative study for a chip design focused on the CLIC tracker, aim is to find a suitable technology and design for a monolithic prototype chip
- ▶ In parallel: new SOI prototype with larger and more uniform matrix has been fabricated and will be tested in beam later this year

# Backup

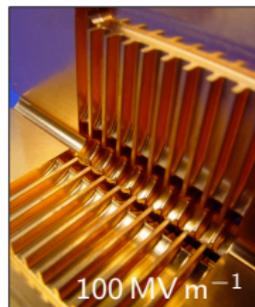
# CLIC

- ▶ CLIC (Compact Linear Collider): linear  $e^+e^-$  collider proposed for the post HL-LHC phase
- ▶ Energy range from a few hundred GeV up to 3 TeV, staged construction
- ▶ Physics goals:
  - ▶ Precision measurements of SM processes (Higgs, top)
  - ▶ Precision measurements of new physics potentially discovered at 14 TeV LHC
  - ▶ Search for new physics: unique sensitivity to particles with electroweak charge

Possible layout near Geneva

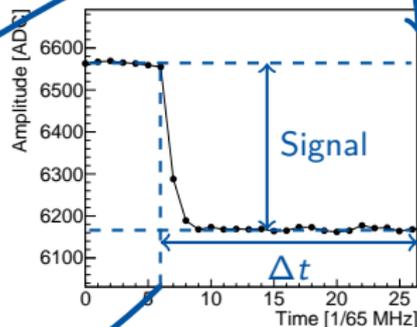
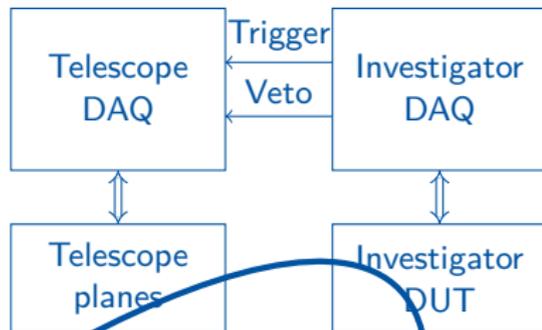
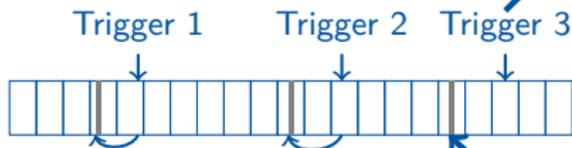


CLIC accelerating structure



# ALICE investigator: Telescope integration

- ▶ 1024 samples/frame/pixel, 65 MHz sampling, self-triggered readout
- ▶ Readout is triggered, if at least one pixel passes a predefined threshold
- ▶ Synchronization of clock domains not easily possible
- ▶ Timetag triggered frame via trigger pulse fed to telescope TDC at the end of frame
- ▶ Use TDC packet in tel. data stream + relative time in investigator frame to assign exact time to hit



# Cracow SOI chip: Telescope integration

- ▶ Source follower matrix investigated in testbeam, rolling shutter readout, 150  $\mu$ s integration time
- ▶ SOI DAQ takes clock and T0, marks begin of readout frame
- ▶ Hit can end up in the current or the next frame, depending on its position relative to the rolling shutter
- ▶ Analysis copies several frames overlaid into each telescope event

